onsemi

Schottky Barrier Diode NSR10F30NXT5G

These Schottky barrier diodes are optimized for low forward voltage drop and low leakage current and are offered in a Chip Scale Package (CSP) to reduce board space. The low thermal resistance enables designers to meet the challenging task of achieving higher efficiency and meeting reduced space requirements.

Features

- Low Forward Voltage Drop 420 mV @ 1.0 A
- Low Reverse Current 20 µA @ 10 V VR
- 1.0 A of Continuous Forward Current
- ESD Rating Human Body Model: Class 3B – Machine Model: Class C
- High Switching Speed
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc-dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

Markets

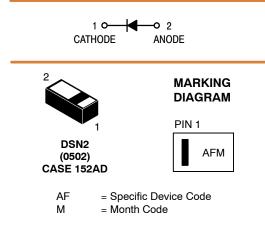
- Mobile Handsets
- MP3 Players
- Digital Camera and Camcorders
- Notebook PCs & PDAs
- GPS

MAXIMUM RATINGS

Rating		Symbol	Value	Unit	
Reverse Voltage		V _R	30	V	
Forward Current	(DC)	١ _F	1.0	А	
Forward Surge C cycle)	Current (60 Hz @ 1	I _{FSM}	18	A	
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)		I _{FRM}	4.0	A	
ESD Rating:	Human Body Model Machine Model	ESD	> 8 > 400	kV V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.





ORDERING INFORMATION

Device	Package	Shipping†
NSR10F30NXT5G	DSN2 (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSR10F30NXT5G

THERMAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Thermal Resistance Junction-to-Ambient (Note 1) Total Power Dissipation @ $T_A = 25^{\circ}C$	$R_{ heta JA}$ P_D			228 548	°C/W mW
Thermal Resistance Junction-to-Ambient (Note 2) Total Power Dissipation @ T _A = 25°C	R _{θJA} P _D			85 1.47	°C/W W
Storage Temperature Range	T _{stg}			-40 to +125	°C
Junction Temperature	TJ			+150	°C

Mounted onto a 4 in square FR-4 board 50 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.
 Mounted onto a 4 in square FR-4 board 1 in sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Leakage $(V_R = 10 \text{ V})$ $(V_R = 30 \text{ V})$	I _R			20 100	μΑ
Forward Voltage $(I_F = 0.5 A)$ $(I_F = 1.0 A)$	V _F		0.400 0.450	0.420 0.470	V

NSR10F30NXT5G

TYPICAL CHARACTERISTICS

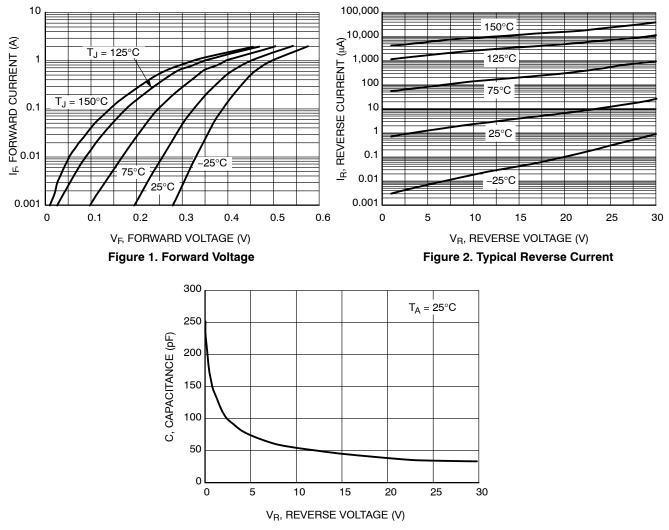
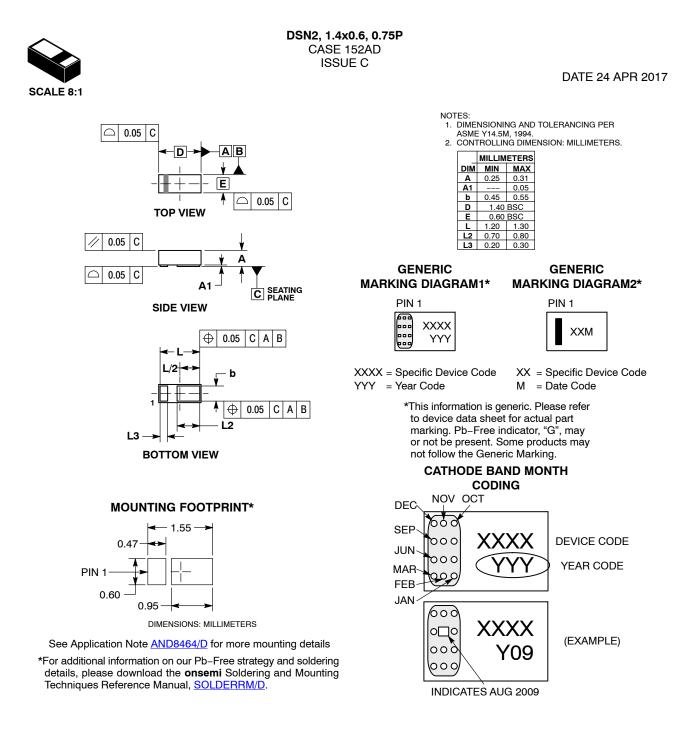


Figure 3. Typical Capacitance





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 DESCRIPTION:
 DSN2, 1.4X0.6, 0.75P
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